

ZXMS6001N3 60V N-channel self protected enhancement mode INTELLIFETTM MOSFET

Summary

Continuous drain source voltage $V_{DS} = 60V$ On-state resistance $675m\Omega$ Max nominal load current (a) $1.1A (V_{IN} = 5V)$ Min nominal load current (c) $0.7A (V_{IN} = 5V)$ Clamping Energy550mJ



Description

Low input current self protected low side MOSFET intended for Vin=5V applications. Monolithic over temperature, over current, over voltage (active clamp) and ESD protected logic level functionality. Intended as a general purpose switch.

Note:

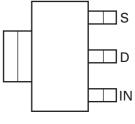
The tab is connected to the source pin and must be electrically isolated from the drain pin. Connection of significant copper to the drain pin is recommended for best thermal performance.

Features

- · Short circuit protection with auto restart
- Over voltage protection (active clamp)
- Thermal shutdown with auto restart
- Over-current protection
- Input protection (ESD)
- Load dump protection (actively protects load)
- · Low input current

Ordering information

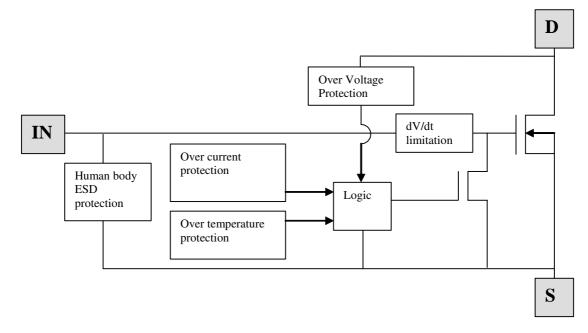
| Device | Package | Part mark | Reel size (inches) | Tape width (mm) | Quantity per reel |
|--------------|---------|-----------|-----------------------|--------------------|----------------------|
| ZXMS6001N3TA | SOT223 | ZXMS6001 | 7 | 12 embossed | 1,000 |



S



Functional block diagram



Applications and information

- Especially suited for loads with a high in-rush current such as lamps and motors.
- All types of resistive, inductive and capacitive loads in switching applications.
- μ C compatible power switch for 12V and 24V DC applications.
- Automotive rated.
- Replaces electromechanical relays and discrete circuits.

Linear Mode capability - the current-limiting protection circuitry is designed to de-activate at low Vds, in order not to compromise the load current during normal operation. The design max DC operating current is therefore determined by the thermal capability of the package/board combination, rather than by the protection circuitry. This does not compromise the products ability to self protect itself at low V_{DS} .

Absolute maximum ratings

| Parameter | Symbol | Limit | Unit |
|--|-----------------------|-----------------------------------|------|
| Continuous Drain-Source Voltage | V _{DS} | 60 | V |
| Drain-Source Voltage for short circuit protection $V_{IN} = 5V$ | V _{DS(SC)} | 36 | V |
| Continuous Input Voltage | V _{IN} | -0.2 +10 | V |
| Peak Input Voltage | V _{IN} | -0.2 +20 | V |
| Continuous Input Current -0.2V=V _{IN} =10V V _{IN} <-0.2V or V _{IN} >10V | I _{IN} | No limit ∣ I _{IN} ≤2 | mA |
| Operating Temperature Range | T _j , | -40 to +150 | °C |
| Storage Temperature Range | T _{stg} | -55 to +150 | °C |
| Power Dissipation at $T_A = 25^{\circ}C^{(a)}$ | PD | 1.5 | W |
| Power Dissipation at $T_A = 25^{\circ}C^{(c)}$ | PD | 0.6 | W |
| Continuous Drain Current @ V _{IN} =5V; T _A =25°C ^(a) | ۱ _D | 1.1 | А |
| Continuous Drain Current @ V _{IN} =5V; T _A =25°C ^(c) | ۱ _D | 0.7 | А |
| Continuous Source Current (Body Diode) ^(a) | ۱ _S | 2.0 | А |
| Pulsed Source Current (Body Diode) ^(b) | ۱ _S | 3.3 | А |
| Unclamped single pulse inductive energy | E _{AS} | 550 | mJ |
| Load dump protection | V _{LoadDump} | 80 | V |
| Electrostatic Discharge (Human Body Model) | V _{ESD} | 4000 | V |
| DIN humidity category, DIN 40 040 | | E | |
| IEC climatic category, DIN IEC 68-1 | | 40/150/56 | |

Thermal resistance

| Parameter | Symbol | Value | Unit |
|------------------------------------|-----------------|-------|------|
| Junction to ambient ^(a) | $R_{\Theta JA}$ | 83 | °C/W |
| Junction to ambient ^(b) | $R_{\Theta JA}$ | 45 | °C/W |
| Junction to ambient ^(c) | $R_{\Theta JA}$ | 208 | °C/W |

NOTES:

(a) For a device surface mounted on 25mm x 25mm x 1.6mm FR4 board with a high coverage of single sided 2oz weight copper. Allocation of 6cm² copper 33% to source tab and 66% to drain pin with source tab and drain pin electrically isolated.

(b) For a device surface mounted on FR4 board as (a) and measured at t<=10s.

(c) For a device surface mounted on FR4 board with the minimum copper required for electrical connections.

Recommended operating conditions

The ZXMS6001 is optimized for use with μ C operating from 5V supplies.

| Symbol | Description | Min | Max | Units |
|-----------------|--|-----|-----|-------|
| V _{IN} | Input voltage range | 0 | 6 | V |
| T _A | Ambient temperature range | -40 | 125 | °C |
| V _{IH} | High level input voltage for MOSFET ^(d) | 4 | 6 | V |
| V _P | Peripheral supply voltage (voltage to which load is referred) | | 60 | V |

Electrical characteristics (at $T_{amb} = 25^{\circ}C$ unless otherwise stated).

| Parameter | Symbol | Min | Тур | Max | Unit | Conditions |
|---|-------------------------------------|-----|-----|-----|------|--|
| Static Characteristics | | | 1 | | 1 | 1 |
| Drain-Source Clamp Voltage | V _{DS(AZ)} | 60 | 70 | 75 | V | I _D =10mA |
| Off state Drain Current | I _{DSS} | | 0.1 | 3 | μA | V _{DS} =12V, V _{IN} =0V |
| Off state Drain Current | I _{DSS} | | 3 | 15 | μA | V _{DS} =32V, V _{IN} =0V |
| Input Threshold Voltage ^(d) | V _{IN(th)} | 1 | 1.8 | 2.5 | V | V _{DS} =V _{GS} , I _D =10mA |
| Input Current | I _{IN} | | 150 | | μA | V _{IN} =+3V |
| Input Current | I _{IN} | | 335 | 500 | μΑ | V _{IN} =+5V, all circumstances |
| Static Drain-Source On-State Resistance | R _{DS(on)} | | 1 | 2 | Ω | V _{IN} =3V, I _D =0.1A |
| Static Drain-Source On-State Resistance | R _{DS(on)} | | 520 | 675 | mΩ | V _{IN} =5V, I _D =0.7A |
| Current Limit ^(e) | I _{D(LIM)} | 1 | 1.8 | 3 | А | V _{IN} =5V, V _{DS} >5V |
| Dynamic Characteristics | | | | | | |
| Turn-On Time (V _{IN} to 90% I _D) | t _{on} | | 27 | 40 | μS | R _L =22Ω, V _{IN} =0 to 5V, V _{DD} =12V |
| Turn-Off time (V _{IN} to 90% I _D) | t _{off} | | 26 | 40 | μS | $R_L=22\Omega$, $V_{IN}=5V$ to 0V, $V_{DD}=12V$ |
| Slew Rate On (70 to 50% V _{DD}) | -dV _{DS} /dt _{on} | | 1.4 | 10 | V/µs | $R_L=22\Omega$, $V_{IN}=0$ to 5V, $V_{DD}=12V$ |
| Slew Rate Off (50 to 70% V _{DD}) | DV _{DS} /dt _{on} | | 1.2 | 10 | V/µs | $R_L=22\Omega$, $V_{IN}=5V$ to 0V, $V_{DD}=12V$ |

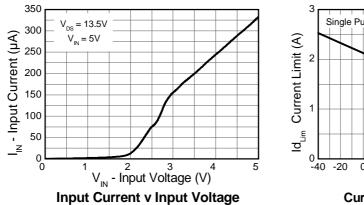
NOTES:

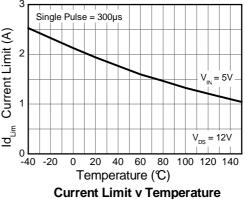
(d) Recommended input voltage range over which protection circuits function as specified.

(e) The drain current is limited to a reduced value when Vds exceeds a safe level

| Parameter | Symbol | Min | Тур | Max | Unit | Conditions |
|---|-------------------|-----|-----|-----|------|---|
| Protection Functions (f) | | | | | | |
| Minimum input voltage for over temperature protection | V _{PROT} | 4 | 3.5 | | V | Ttrip>150°C |
| Maximum input voltage for over temperature protection | V _{PROT} | | 7 | 6 | V | Ttrip>150°C |
| Thermal Overload Trip Temperature | T _{JT} | 150 | 175 | | °C | |
| Thermal hysteresis | | | 8 | | °C | |
| Unclamped single pulse inductive energy Tj=25°C | E _{AS} | 550 | | | mJ | I _{D(ISO)} =0.7A, V _{DD} =32V |
| Unclamped single pulse inductive energy Tj=150°C | E _{AS} | 200 | | | mJ | I _{D(ISO)} =0.7A, V _{DD} =32V |
| Inverse Diode | | | | | | |
| Source drain voltage | V _{SD} | | | 1 | V | V _{IN} =0V, -I _D =1.4A |

f Integrated protection functions are designed to prevent IC destruction under fault conditions described in the datasheet. Fault conditions are considered as "outside" normal operating range. Protection functions are not designed for continuous, repetitive operation.





Application information

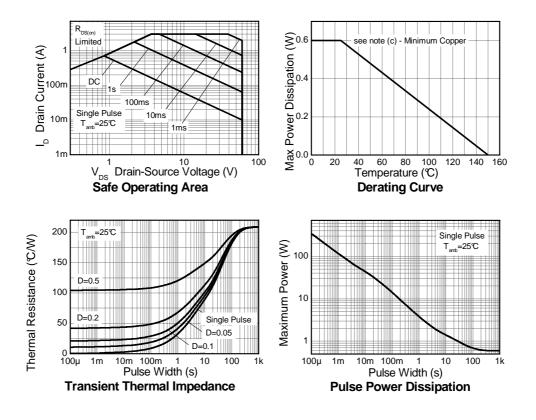
The current-limit protection circuitry is designed to de-activate at low Vds to prevent the load current from being unnecessarily restricted during normal operation. The design max DC operating current is therefore determined by the thermal capability of the package/board combination, rather than by the protection circuitry (see graph page 8 'typical output characteristic'). This does not compromise the products ability to self protect at low V_{DS}.

The overtemperature protection circuit trips at a minimum of 150°C. So the available package dissipation reduces as the maximum required ambient temperature increases. This leads to the following maximum recommended continuous operating currents.

Minimum copper area characteristics

For minimum copper condition as described in note (c)

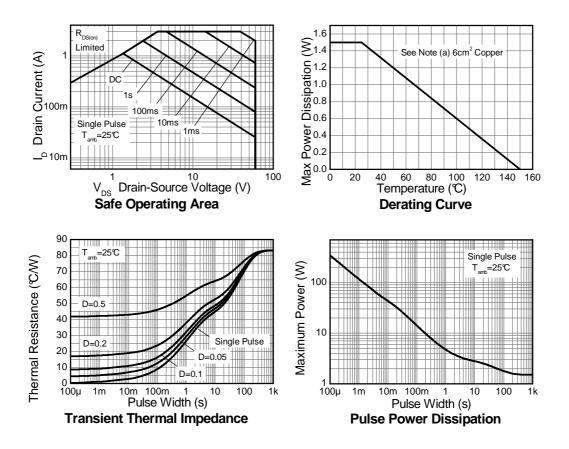
| Max Ambient Temperature T _A | Maximum continuous current V _{IN} =5V |
|--|---|
| | |
| 25°C at Vin=5V | 720 |
| 70°C at Vin=5V | 575 |
| 85°C at Vin=5V | 520 |
| 125°C at Vin=5V | 320 |

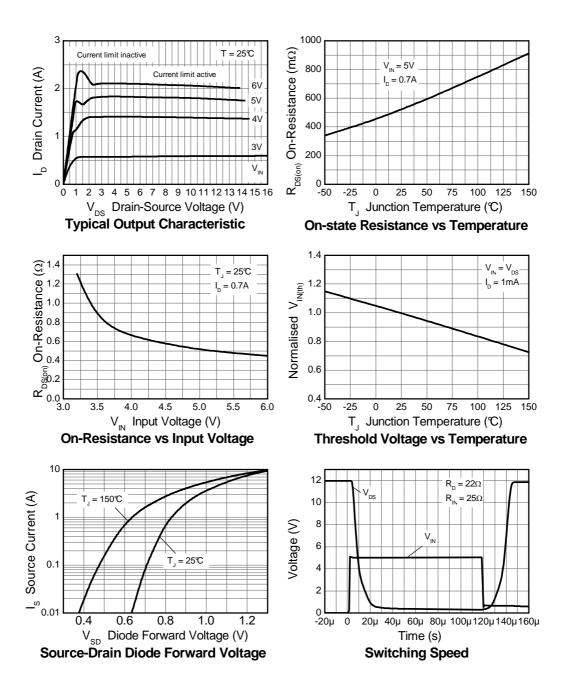


Large copper area characteristics

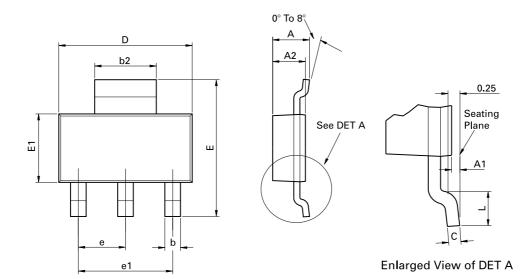
For large copper area as described in note (a)

| Max Ambient Temperature T _A | Maximum continuous current V _{IN} =5V |
|--|---|
| | |
| 25°C at Vin=5V | 1140 |
| 70°C at Vin=5V | 915 |
| 85°C at Vin=5V | 825 |
| 125°C at Vin=5V | 510 |





Package outline - SOT223



Conforms to JEDEC TO-261 AA Issue B

| Dim. | Millin | Millimeters | | Inches | | Millin | neters | Inc | hes |
|-------|--------|-------------|--------|--------|------|----------|--------|-----------|-------|
| Dini. | Min. | Max. | Min. | Max. | Dim. | Min. | Max. | Min. | Max. |
| A | - | 1.80 | - | 0.071 | D | 6.30 | 6.70 | 0.248 | 0.264 |
| A1 | 0.02 | 0.10 | 0.0008 | 0.004 | е | 2.30 | BSC | 0.090 | 5 BSC |
| A2 | 1.55 | 1.65 | 0.0610 | 0.0649 | e1 | 4.60 BSC | | 0.181 BSC | |
| b | 0.66 | 0.84 | 0.026 | 0.033 | E | 6.70 | 7.30 | 0.264 | 0.287 |
| b2 | 2.90 | 3.10 | 0.114 | 0.122 | E1 | 3.30 | 3.70 | 0.130 | 0.146 |
| С | 0.23 | 0.33 | 0.009 | 0.013 | L | 0.90 | - | 0.355 | - |

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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